

**SEMICONDUCTOR MEMORY DEVICE HAVING COLUMN SELECT LINE
DRIVING SCHEME FOR REDUCING SKEW BETWEEN COLUMN SELECT LINES
AND COLUMN SELECT LINE DRIVING METHOD THEREOF**

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BACKGROUND OF THE INVENTION

This application claims the priority of Korean Patent Application No. 2003-22571, filed on April 10, 2003, in the Korean Intellectual Property Office, the disclosure of which is incorporated herein in its entirety by reference.

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1. Field of the Invention

The present invention relates to a semiconductor memory device, and more particularly, to a semiconductor memory device capable of reducing skew between column select lines (CSLs) and a CSL driving method

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2. Description of the Related Art

In dynamic random access memory (DRAM), an external address is decoded to generate a column address, and column select lines (CSLs) for memory cells are selected using the column address. Thus, it is important to reduce skew between the CSLs during selection of the CSLs so as to improve write and read operation speeds.

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FIG. 1 is a block diagram illustrating a structure of a conventional semiconductor memory device with a CSL driving scheme. Referring to FIG. 1, a CSL enable master signal generator *A11* receives an internal clock *PCLKC* and generates a CSL enable master signal *EM*, and a CSL disable master signal generator *B11* receives the internal clock *PCLKC* and generates a CSL disable master signal *DM*. The internal clock *PCLKC* is generated from an external clock applied from outside the semiconductor memory device.

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Next, a CSL enable controller *E11* generates a CSL enable control signal *EC* in response to the CSL enable master signal *EM* and a CSL disable controller *F11* generates a CSL disable control signal *DC* in response to the CSL disable master signal *DM*.

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Next, a plurality of CSL drivers *G11* through *G14* drive CSLs *CSL1* through *CSL4* of a plurality of memory cell arrays *H11* through *M14*, respectively, in response to a decoded column address (not shown), the CSL enable control signal *EC*, and the CSL disable control signal *DC*.

5 The conventional CSL driving scheme uses one CSL enable controller *E11* and one CSL disable controller *F11* so as to control all of the CSL drivers *G11* through *G14*. As a result, a line for transmitting the signal *EC* output from the CSL enable controller and a line for transmitting the signal *DC* output from the CSL disable controller *F11* are globally routed to all of the CSL drivers *G11* through *G14*.

10 Accordingly, the loads on input terminals of the CSL drivers *G11* through *G14* depend on the positions of the memory cell arrays *H11* through *H14* and the CSL drivers *G11* through *G14*. An increase in the load increases skew between the CSLs *CSL1* through *CSL4*. This phenomenon places restrictions on improvement of write and read operation speeds of the semiconductor memory device.

15 SUMMARY OF THE INVENTION

The present invention provides a semiconductor memory device with a column select line (CSL) driving scheme capable of reducing skew between CSLs.

20 The present invention also provides a method of driving CSLs of a semiconductor memory device so as to reduce skew between the CSLs.

According to an aspect of the present invention, there is provided a semiconductor memory device comprising a plurality of memory cell arrays; an enable master signal generator which receives a predetermined signal and generates a column select line enable master signal; a disable master signal generator which receives the predetermined signal and generates a column select line disable master signal; a plurality of enable master signal delayers which delay the column select line enable master signal; a plurality of disable master signal delayers which delay the column select line disable master signal; a plurality of column select line enable controllers which generate column select line enable control signals, respectively, in response to signals output from the enable master signal delayers; a plurality of column select line disable controllers which generate column select line disable control signals,

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respectively, in response to signals output from the disable master signal delayers; and a plurality of column select line drivers which drive column select lines of the related memory cell arrays, respectively, in response to signals output from the column select line enable controllers and signals output from the column select line disable controllers.

5 In particular, the plurality of CSL enable controllers and the plurality of CSL disable controllers are installed around the CSL drivers. Signal delay times delayed by the enable master signal delayers can be different from one another, and signal delay times delayed by the disable master signal delayers can be different from one another. In one embodiment, the predetermined signal is an internal clock generated from an
10 external clock that is applied from the outside of the semiconductor memory device.

In one embodiment, the column select line enable controllers respond to a decoded column address. In one embodiment, the column select line disable controllers respond to a decoded column address.

According to another aspect of the present invention, there is provided a method
15 of driving column select lines of a semiconductor memory device with a plurality of memory cell arrays, the method comprising receiving a predetermined signal and generating a column select line enable master signal; receiving the predetermined signal and generating a column select line disable master signal; generating a plurality of delayed column select line enable master signals by delaying the column select line
20 enable master signal for different times; generating a plurality of delayed column select line disable master signals by delaying the column select line disable master signal for different times; generating a plurality of column select line enable control signals in response to the delayed column select line enable master signals; generating a plurality of column select line disable control signals in response to the delayed column select
25 line disable master signals; and driving the column select lines of the memory cell arrays in response to the column select line enable control signals and the column select line disable control signals, respectively.

in one embodiment, the predetermined signal is an internal clock generated from an external clock applied from the outside of the semiconductor memory device.

BRIEF DESCRIPTION OF THE DRAWINGS

The foregoing and other objects, features and advantages of the invention will be apparent from the more particular description of a preferred embodiment of the invention, as illustrated in the accompanying drawings in which like reference characters refer to the same parts throughout the different views. The drawings are not necessarily to scale, emphasis instead being placed upon illustrating the principles of the invention.

FIG. 1 is a block diagram illustrating a structure of a conventional semiconductor memory device with a column select line (CSL) driving scheme.

FIG. 2 illustrates a structure of a semiconductor memory device according to a preferred embodiment of the present invention.

FIG. 3 illustrates detailed circuit constructions of a CSL enable master signal generator and a CSL disable master signal generator shown in FIG. 2.

FIG. 4 illustrates detailed circuit constructions of a plurality of enable master signal delayers of FIG. 2.

FIG. 5 illustrates detailed circuit constructions of a plurality of disable master signal delayers of FIG. 2.

FIG. 6 illustrates detailed circuit constructions of a plurality of CSL enable controllers of FIG. 2.

FIG. 7 illustrates detailed circuit constructions of a plurality of CSL disable controllers of FIG. 2.

FIG. 8 illustrates detailed circuit constructions of a plurality of CSL drivers of FIG. 2.

DETAILED DESCRIPTION OF THE INVENTION

FIG. 2 illustrates a semiconductor memory device according to a preferred embodiment of the present invention. The semiconductor memory device of FIG. 2 operates according to a column select line (CSL) driving method according to the present invention. Referring to FIG. 2, the semiconductor memory device according to a preferred embodiment of the present invention includes a plurality of memory cell arrays *H21* through *H24*, a CSL enable master signal generator *A21*, a CSL disable master signal generator *B21*, a plurality of enable master signal delayers *C21* through

C24, a plurality of disable master signal delayers *D21* through *D24*, a plurality of CSL enable controllers *E21* through *E24*, a plurality of CSL disable controllers *F21* through *F24*, and a plurality of CSL drivers *G21* through *G24*.

Unlike the conventional semiconductor memory device of FIG. 1, the semiconductor memory device according to the present invention includes the plurality of CSL enable controllers *E21* through *E24* and the plurality of CSL disable controllers *F21* through *F24* installed in proximity to CSL drivers *G21* through *G24*. Also, a plurality of enable master signal delayers *C21* through *C24* are installed between the plurality of CSL enable controllers *E21* through *E24* and the CSL enable master signal generator *A21*. The plurality of disable master signal delayers *D21* through *D24* are installed between the plurality of CSL disable controllers *F21* through *F24* and the CSL disable master signal generator *B21*.

The CSL enable master signal generator *A21* receives an internal clock *PCLKC* and generates a CSL enable master signal *EM*. The CSL disable master signal generator *B21* receives the internal clock *PCLKC* and generates a CSL disable master signal *DM*. The internal clock *PCLKC* is made from an external clock applied from the outside of the semiconductor memory device.

The plurality of enable master signal delayers *C21* through *C24* delay the CSL enable master signal *EM* for different times to generate a plurality of delayed CSL enable master signals *DEM1* through *DEM4*, respectively. The plurality of disable master signal delayers *D21* through *D24* delay the CSL disable master signal *DM* for different times to generate a plurality of delayed CSL disable master signals *DDM1* through *DDM4*, respectively.

The plurality of CSL enable controllers *E21* through *E24* generates a plurality of CSL enable control signals *EC1* through *EC4* in response to the plurality of delayed CSL enable master signals *DEM1* through *DEM4* and a decoded column address (not shown). The plurality of CSL disable controllers *F21* through *F24* generates a plurality of CSL disable control signals *DC1* through *DC4* in response to the plurality of delayed CSL disable master signals *DDM1* through *DDM4* and a decoded column address (not shown).

The plurality of the CSL drivers *G21* through *G24* drive the memory cell arrays *H21* through *H24* in response to the CSL enable control signals *EC1* through *EC4* and the CSL disable control signals *DC1* through *DC4*, respectively.

FIG. 3 shows detailed circuit diagrams of the CSL enable master signal generator *A21* and the CSL disable master signal generator *B21* of FIG. 2. Referring to FIG. 3, the CSL enable master signal generator *A21* includes an even number of inverters 301 through 304 that are connected in series. The CSL enable master signal generator *A21* is a kind of delayer that delays the internal clock *PCLKC* for a predetermined time to generate the CSL enable master signal *EM*.

The CSL disable master signal generator *B21* includes an odd number of inverters 305 through 309 that are connected in series. The CSL disable master signal generator *B21* is a kind of inverting delayer that inverts the internal clock *PCLKC* and delays it for a predetermined time in order to obtain the CSL disable master signal *DM*.

FIG. 4 illustrates circuit diagrams of the plurality of the enable master signal delayers *C21* through *C24*. Referring to FIG. 4, the enable master signal delayer *C21* includes an inverter 401 and the enable master signal delayer *C22* includes three inverters 402 through 404. The enable master signal delayer *C23* includes five inverters 405 through 409 and the enable master signal delayer *C24* includes seven inverters 410 through 416. The reason for setting the enable master signal delayers *C21* through *C24* to have different total numbers of inverters is to make these delayers delay the CSL enable master signal *EM* for different times. Thus, the number of inverters included in each enable master signal delayer is not limited.

FIG. 5 illustrates circuit diagrams of the plurality of the disable master signal delayers *D21* through *D24* of FIG. 2. Referring to FIG. 5, the disable master signal delayer *D21* includes an inverter 501 and the disable master signal delayer *D22* includes three inverters 502 through 504. The disable master signal delayer *D23* includes five inverters 505 through 509 and the disable master signal delayer *D24* includes seven inverters 510 through 516. Likewise, the total number of inverters included in each disable master signal delayer is not limited.

FIG. 6 illustrates circuit diagrams of the plurality CSL enable controllers *E21* through *E24*. Referring to FIG. 6, each of the CSL enable controllers *E21* through *E24* includes inverters 601 through 610 and NAND gates 611 through 618.

The CSL enable controller *E21* is activated when the delayed CSL enable master signal *DEM1* is at logic "high" and generates the CSL enable control signal *EC1* in response to decoded column addresses *CA1B* and *CA2B*. The CSL enable controller *E22* is activated when the delayed CSL enable master signal *DEM2* is at logic "high" and generates the CSL enable control signal *EC2* in response to the decoded column addresses *CA1B* and *CA2*.

The CSL enable controller *E23* is activated when the delayed CSL enable master signal *DEM3* is at logic "high" and generates the CSL enable control signal *EC3* in response to the decoded column addresses *CA1B* and *CA2*. The CSL enable controller *E24* is activated when the delayed CSL enable master signal *DEM4* is at logic "high" and generates the CSL enable control signal *EC4* in response to the decoded column addresses *CA1B* and *CA2*.

FIG. 7 illustrates circuit diagrams of the plurality of CSL disable controllers *F21* through *F24*. As shown in FIG. 7, each of the CSL disable controllers *F21* through *F24* includes a NAND gate 701, 702, 703, and 704, respectively.

The CSL disable controller *F21* NANDs the delayed CSL disable master signal *DDM1* and a decoded column address, i.e., a bank select signal *BS1*, to generate the CSL disable control signal *DC1*. The CSL disable controller *F22* NANDs the delayed CSL disable master signal *DDM2* and a bank select signal *BS2* to generate the CSL disable control signal *DC2*.

The CSL disable controller *F23* NANDs the delayed CSL disable master signal *DDM3* and a bank select signal *BS3* to generate the CSL disable control signal *DC3*. The CSL disable controller *F24* NANDs the delayed CSL disable master signal *DDM4* and a bank select signal *BS4* to generate the CSL disable control signal *DC4*.

FIG. 8 illustrates circuit diagrams of the plurality of the CSL drivers *G21* through *G24*. Referring to FIG. 8, each of the CSL drivers *G21* through *G24* includes a NAND gate 801, inverters 802 and 803, a PMOS transistor 804, and NMOS transistors 805 through 808.

The CSL driver G21 enables the CSL CSL1 to logic "high" when the CSL enable control signal EC1 is at logic "high" and the CSL disable control signal DC1 is at logic "low", and disables the CSL CSL1 to logic "low" when the CSL enable control signal EC1 is at logic "low" and the CSL disable control signal DC1 is at logic "high". The
5 CSL driver G22 enables the CSL CSL2 to logic "high" when the CSL enable control signal EC2 is at logic "high" and the CSL disable control signal DC2 is at logic "low" and disables the CSL CSL2 to logic "low" when the CSL enable control signal EC2 is at logic "low" and the CSL disable control signal DC2 is at logic "high".

The CSL driver G23 enables the CSL CSL3 to logic "high" when the CSL enable control signal EC3 is at logic "high" and the CSL disable control signal DC3 is at logic "low", and disables the CSL CSL3 to logic "low" when the CSL enable control signal EC3 is at logic "low" and the CSL disable control signal DC3 is at logic "high". The
10 CSL driver G24 enables the CSL CSL4 to logic "high" when the CSL enable control signal EC4 is at logic "high" and the CSL disable control signal DC4 is at logic "low" and
15 disables the CSL CSL4 to logic "low" when the CSL enable control signal EC4 is at logic "low" and the CSL disable control signal DC4 is at logic "high".

As described above, unlike the conventional semiconductor memory device, a semiconductor memory device according to the present invention includes the plurality of CSL enable controllers E21 through E24 and the plurality of CSL disable controllers
20 F21 through F24 installed around the CSL drivers G21 through G24. Accordingly, loads on input terminals of the CSL drivers G21 through G24 can be almost the same, thereby reducing enable and disable skews between the CSLs CSL1 through CSL4.

Also, the semiconductor memory device according to the present invention includes the plurality of the enable master signal delayers C21 through C24 between
25 the plurality of CSL enable controllers E21 through E24 and the CSL enable master signal generator A21. In particular, since signal delay times delayed by the enable master signal delayers C21 through C24 are set differently, it is possible to compensate for signal delay caused by different loads on signal transmission lines, of a
high-integration memory device, which are used for transmitting the CSL enable master
30 signal EM and the delayed CSL enable master signals DEM1 through DEM4.
Accordingly, enable skew between the CSLs CSL1 through CSL4 can be reduced.

Also, the semiconductor memory device according to the present invention includes the plurality of disable master signal delayers *D21* through *D24* between the plurality of CSL disable controllers *F21* through *F24* and the CSL disable master signal generator *B21*. Similarly, since signal delay times delayed by the disable master signal delayers *D21* through *D24* are set differently, it is possible to compensate for signal delay caused by different loads on signal transmission lines, of a high-integration memory device, for transmitting the CSL disable master signal *DM* and the delayed CSL disable master signals *DDM1* through *DDM4*. Thus, enable skew between the CSLs *CSL1* through *CSL4* can be reduced.

Accordingly, during a read operation, it is possible to spend the same amount of time to sense data in the respective memory cell arrays *H21* through *H24*, using input/output lines, regardless of the positions of the memory cell arrays *H21* through *H24*. As a result, it is possible to minimize skew caused by data sensing and improving write operation speed of the semiconductor memory device. Further, during a write operation, it is possible to make points of time when a CSL is enabled and disabled the same regardless of the positions of the memory cell arrays *H21* through *H24*, thereby improving a write operation speed.

As described above, a semiconductor memory device according to the present invention improves read and write operation speeds by reducing skew between CSLs.

While this invention has been particularly shown and described with reference to preferred embodiments thereof, it will be understood by those skilled in the art that various changes in form and details may be made therein without departing from the spirit and scope of the invention as defined by the appended claims.